Pictures to: 4. IBM T.J. Watson Research Center

4.1 TEM of Silicon - Silicide Interfaces Publication 43

What follows are rthe pictures to publications 43 (*Transmission electron microscopy investigation of silicide formation on slightly oxidized silicon substrates*) I alos add some auxiliary pictures

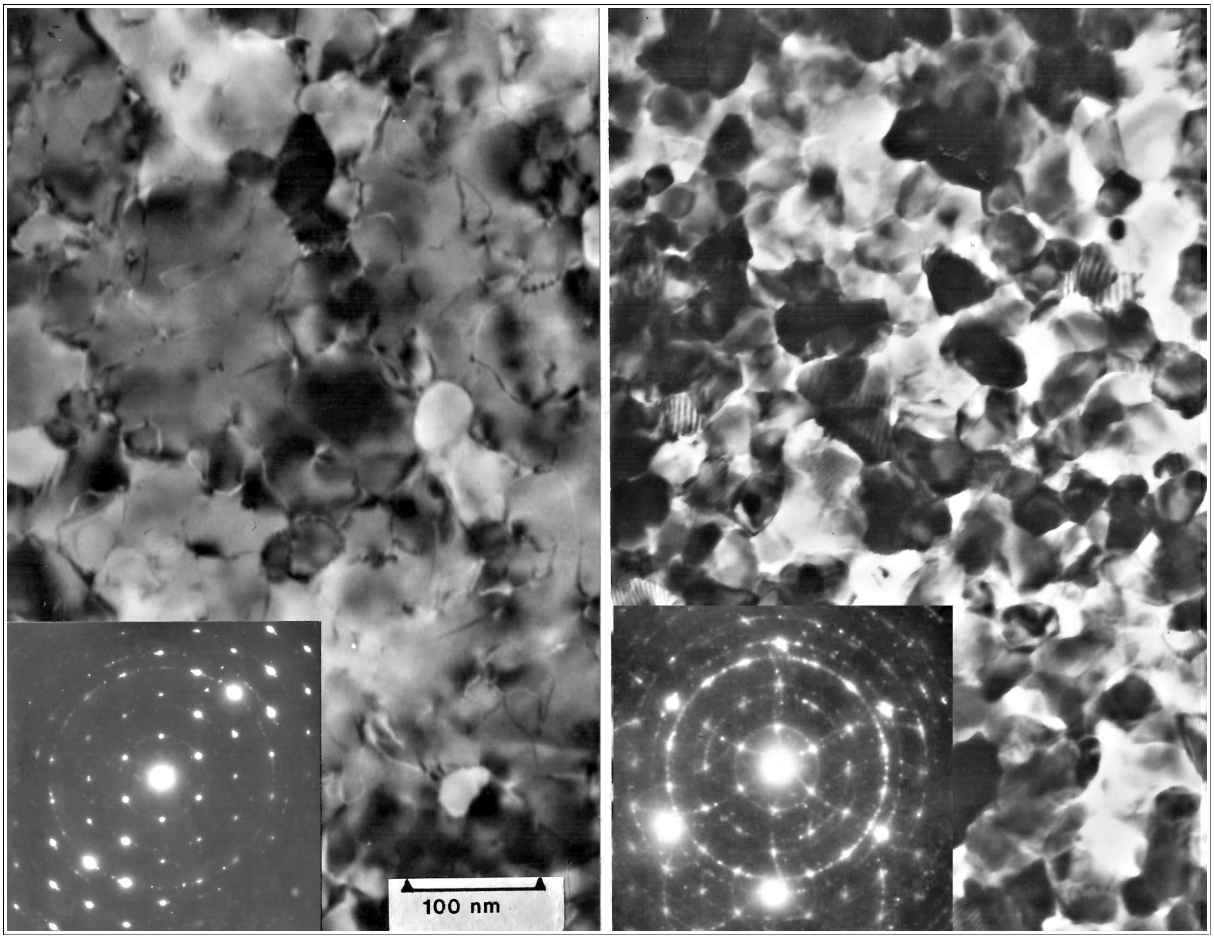

Fig. 1 in Publication 3

FIG.1. (a; left) Pd_2Si film on theclean substrate. (b) Pd_2Si filmon the oxidized substrate.

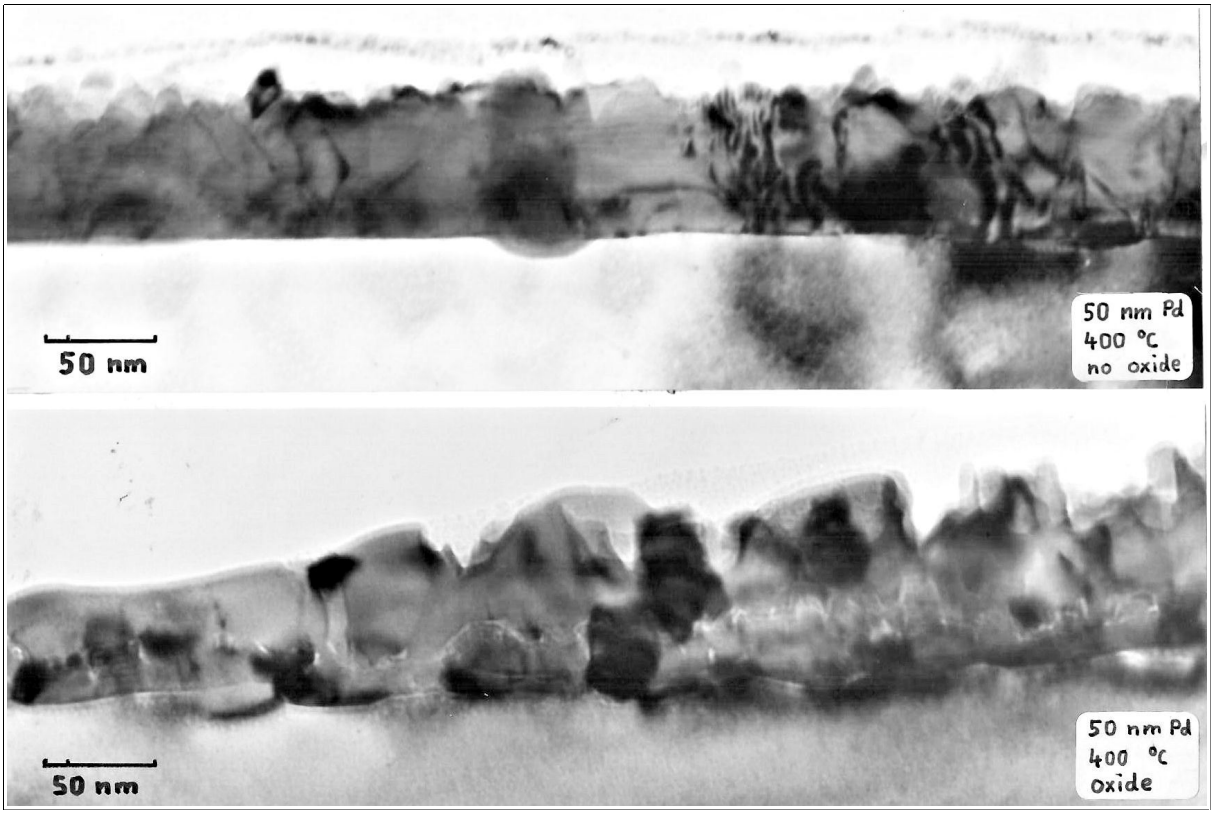

Fig. 2 In Publication 3

FIG.2. (a) Cross-sectional view of Pd $_2$Si on the clean substrate. (b) Cross-sectional view of PtSi on the oxidized substrate.

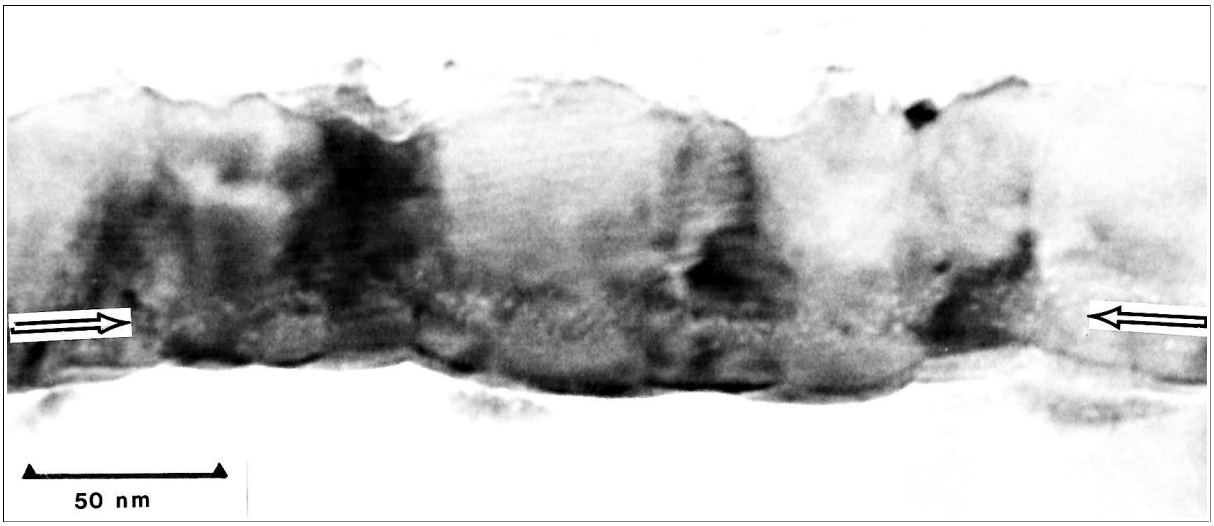

Fig. 3 In Publication 3

FIG. 3. Band of oxide remnants (bettween arrows at about 1/4-1/3 from thesilicide-Si interface) in Pd2Si on a {l00} oriented clean substrate

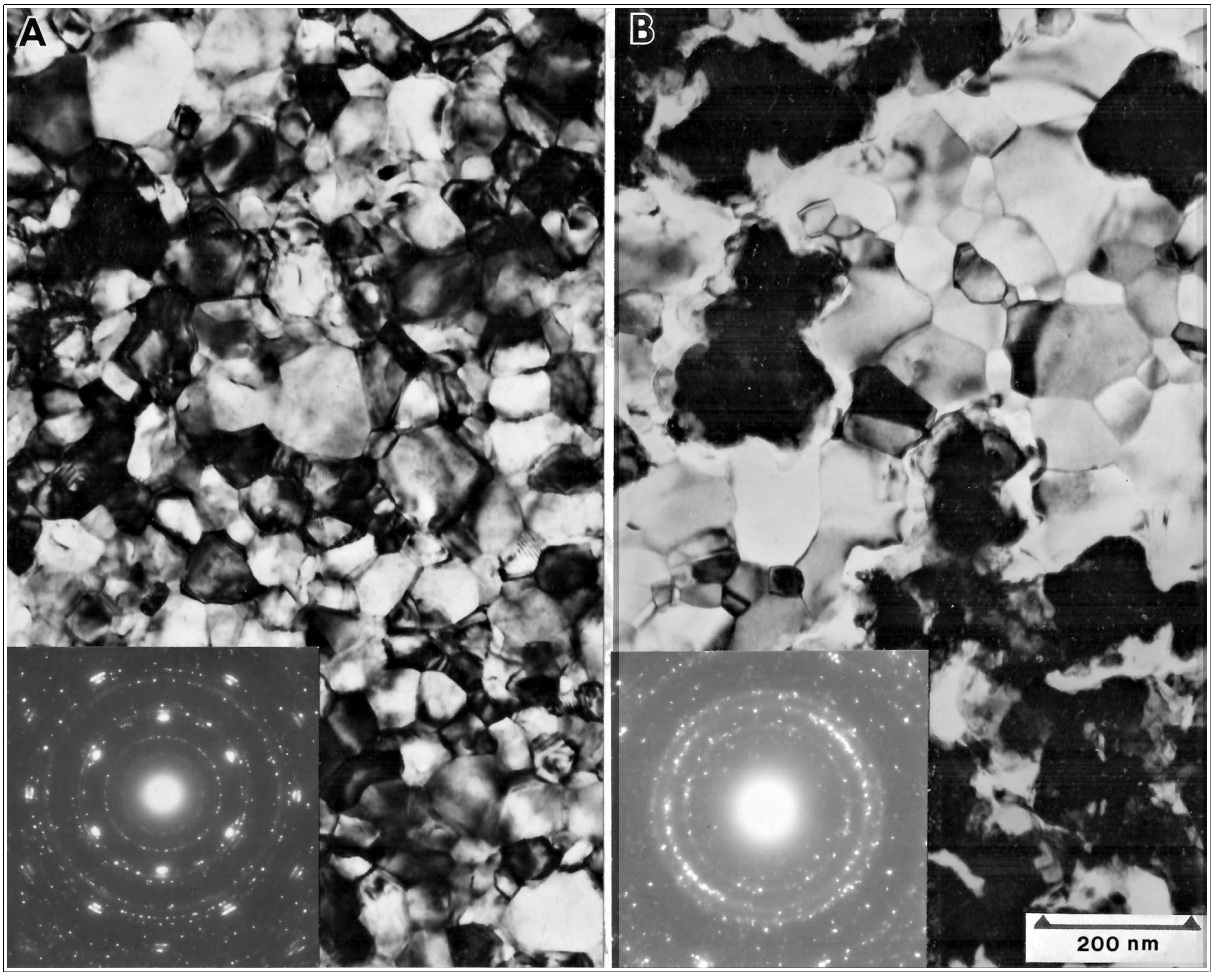

Fig. 6 in Publication 3

FIG. 6. (a) PtSi on the clean sub-strate. (b) Unreacted Pt and PtSi onthe oxidized substrate

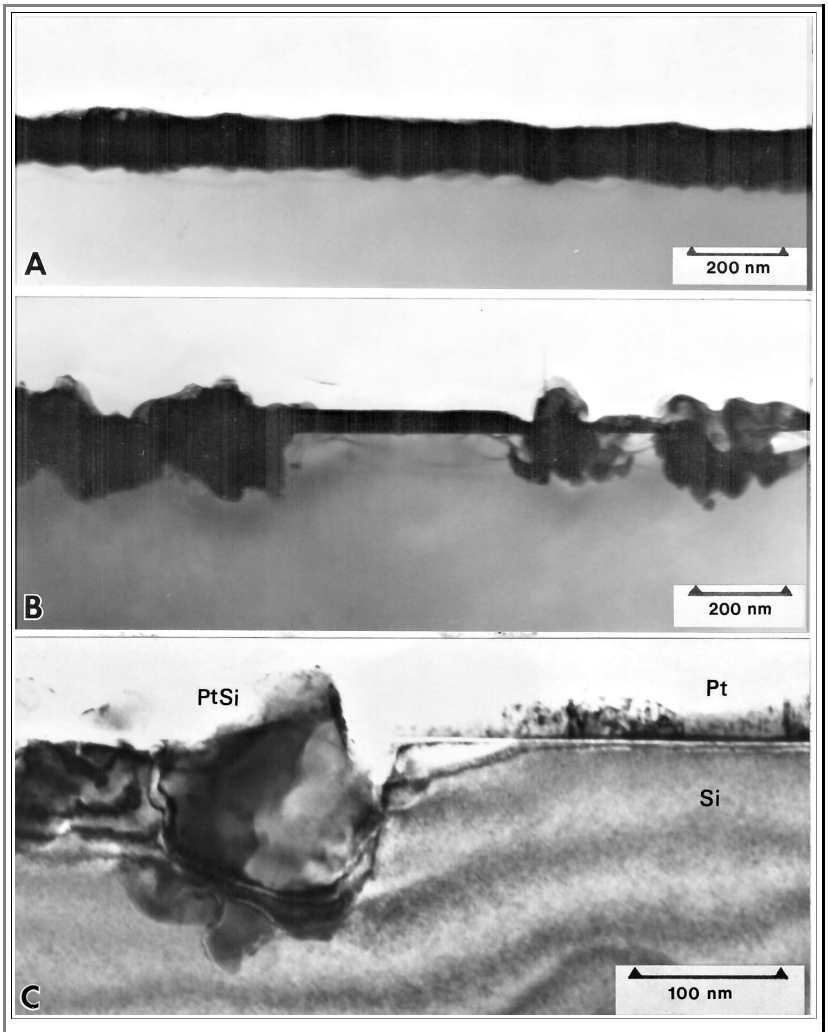

Fig. 7 in Publication 3.

FIG. 7. (a) Cross-sectional view of PtSi on the clean substrate.(b) Cross-sectiooal view cf the unreacted Pt and PtSi on theoxidized substrate. (c) Enlarged view of Fig. 7(b); note the bright band between the unreacted Pt and the Si substrate

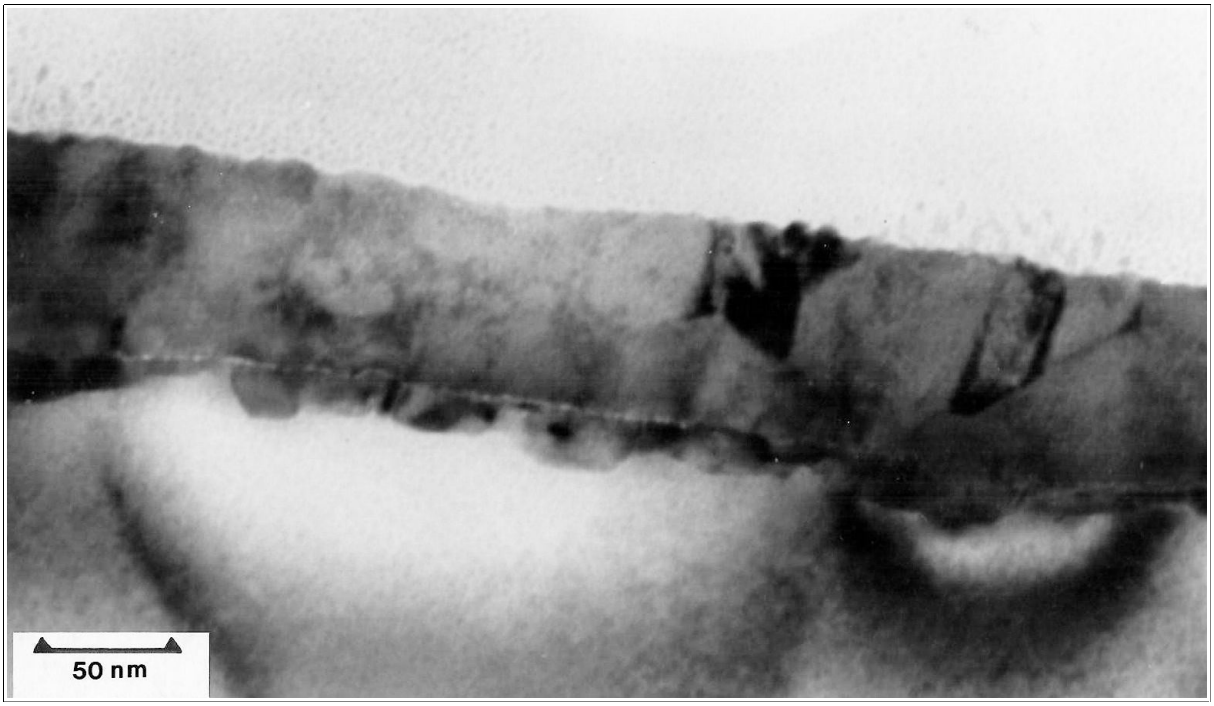

Fig. 8 in Publication 3

FIG.8. PtSi formed by co-evaporation of $Pt_{67}Si_{33}$ on a clean substrate